

6A Avg.

65 Volts

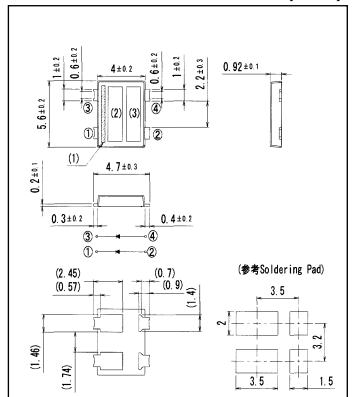
SBD

NB06QSA065

■最大定格 Maximum Ratings

Item	Symbol	Conditions		Unit
くり返しピーク逆電圧 Repetitive Peak Reverse Voltage	V_{RRM}	65		V
平均整流電流 Average Rectified Forward Current	I_O	50Hz, 正弦半波通電抵抗負荷 50Hz Half Sine Wave Resistive Load *1	$T_a=27^{\circ}C^{*2}$ $V_{RM}=30V$	2.8
			$T_l=81^{\circ}C$ Tl:lead Temperature $V_{RM}=30V$	6.0
実効順電流 R.M.S. Forward Current	$I_F(RMS)$	6.66		A
サージ順電流 Surge Forward Current	I_{FSM}	60 50Hz正弦半波, 1サイクル, 非くり返し 50Hz Half Sine Wave, 1cycle, Non-repetitive		A
動作接合温度範囲 Operating Junction Temperature Range	T_{jw}	-40~+150		$^{\circ}C$
保存温度範囲 Storage Temperature Range	T_{stg}	-40~+150		$^{\circ}C$

■OUTLINE DRAWING(mm)



■APPROX. NET WEIGHT:0.06 g

■電氣的・熱的特性 Electrical/Thermal Characteristics

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
ピーク逆電流 Peak Reverse Current	I_{RM}	$T_j=25^{\circ}C, V_{RM}=65V,$ 一素子あたり Per Diode	—	—	300	μA
ピーク順電圧 Peak Forward Voltage	V_{FM}	$T_j=25^{\circ}C, I_{FM}=3A,$ 一素子あたり Per Diode	—	—	0.61	V
熱抵抗 Thermal Resistance	$R_{th(j-a)}$	接合部・周囲間 Junction to Ambient	—	—	60	$^{\circ}C/W$
	$R_{th(j-l)}$	接合部・リード間 Junction to Lead	—	—	7	$^{\circ}C/W$

*1 カソード共通動作による/Common Cathode Operation

*2 ガラエポ基板実装/Glass-Epoxy Substrate mounted (Soldering Lands= 2.0 × 1.5 mm, 2.0 × 3.5 mm, Both Sides)

■定格・特性曲線

FIG.1 順電圧特性
FORWARD CURRENT VS. VOLTAGE

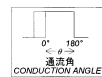
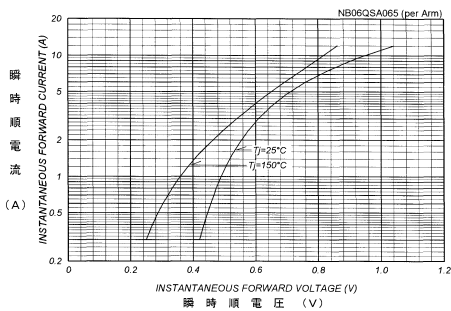


FIG.2 平均順電力損失特性
AVERAGE FORWARD POWER DISSIPATION

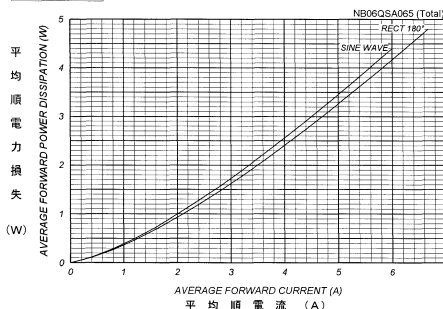


FIG.3 ピーク逆電流 - ピーク逆電圧特性
PEAK REVERSE CURRENT VS. PEAK REVERSE VOLTAGE

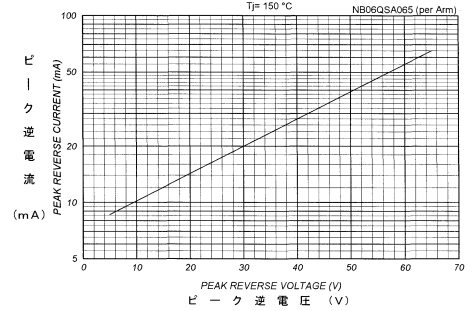


FIG.4 平均逆電力損失
AVERAGE REVERSE POWER DISSIPATION

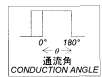
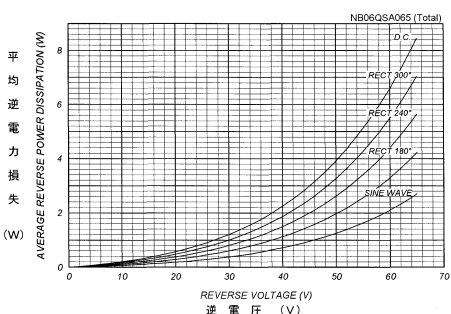


FIG.5 平均順電流 - リード温度定格
AVERAGE FORWARD CURRENT VS. LEAD TEMPERATURE

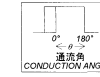
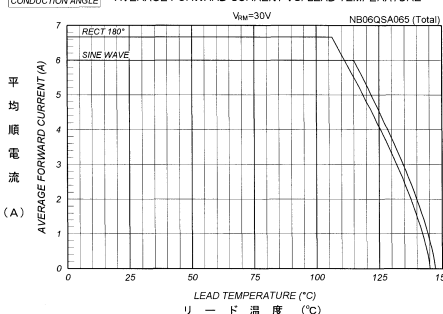


FIG.6 平均順電流 - 周囲温度定格
AVERAGE FORWARD CURRENT VS. AMBIENT TEMPERATURE

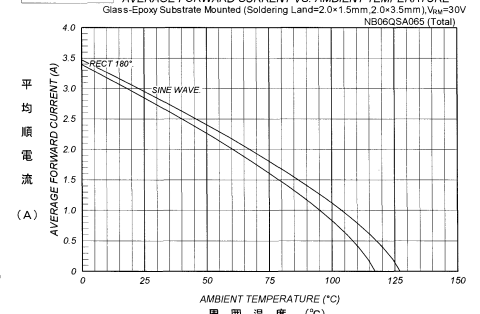


FIG.7 サージ順電流定格
SURGE CURRENT RATINGS

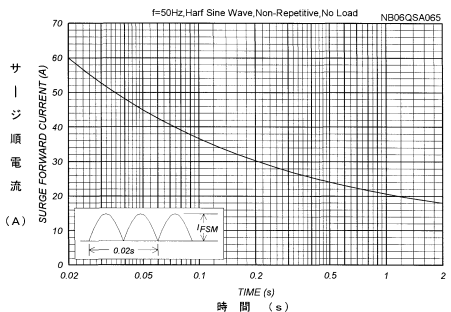


FIG.8 接合容量特性
JUNCTION CAPACITANCE VS. REVERSE VOLTAGE

